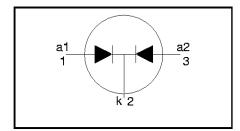
PBYR20100CT, PBYR20100CTB series

FEATURES

- · Low forward volt drop
- Fast switching
- · Reverse surge capability
- · High thermal cycling performance
- · Low thermal resistance

SYMBOL



QUICK REFERENCE DATA

$$V_R = 60 \text{ V/ } 80 \text{ V/ } 100 \text{ V}$$

$$I_{O(AV)} = 20 \text{ A}$$

$$V_F \le 0.7 \text{ V}$$

GENERAL DESCRIPTION

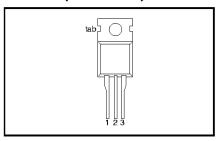
Dual, common cathode schottky rectifier diodes in a conventional leaded plastic package and a surface mounting plastic package. Intended for use as output rectifiers in low voltage, high frequency switched mode power supplies.

The PBYR20100CT series is supplied in the SOT78 conventional leaded package. The PBYR20100CTB series is supplied in the SOT404 surface mounting package.

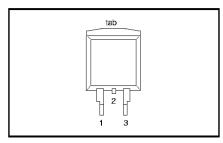
PINNING

PIN	DESCRIPTION		
1	anode 1 (a)		
2	cathode (k) 1		
3	anode 2 (a)		
tab	cathode (k)		

SOT78 (TO220AB)



SOT404



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	I. MAX.			UNIT
		PBYR20 PBYR20		60CT 60CTB	80CT 80CTB	100CT 100CTB	
V _{RRM}	Peak repetitive reverse voltage		-	60	80	100	٧
V _{RWM}	Working peak reverse voltage		-	60	80	100	٧
V_{R}	Continuous reverse voltage	T _{mb} ≤ 139 °C	-	60	80	100	٧
I _{O(AV)}	Average rectified output current (both diodes conducting)	square wave; $\delta = 0.5$; $T_{mb} \le 133$ °C	-		20		Α
I _{FRM}	Repetitive peak forward current per diode	square wave; $\delta = 0.5$; $T_{mb} \le 133 ^{\circ}C$	-		20		Α
I _{FSM}	Non-repetitive peak forward current per diode	t = 10 ms t = 8.3 ms sinusoidal; T _j = 125 °C prior to surge; with reapplied V _{RRM(max)}	-		135 150		A A
I _{RRM}	Peak repetitive reverse surge current per diode	pulse width and repetition rate limited by T _{max}	-		1		Α
T_{j}	Operating junction temperature	· Jilliax	-		150		,C
T_{stg}	Storage temperature		- 65		175		°C

^{1.} It is not possible to make connection to pin 2 of the SOT404 package.

PBYR20100CT, PBYR20100CTB series

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{\text{th }j\text{-mb}}$ $R_{\text{th }j\text{-a}}$	to mounting base	per diode both diodes SOT78 package in free air SOT404 package, pcb mounted, minimum footprint, FR4 board		- - 60 50	2 1 -	K/W K/W K/W

ELECTRICAL CHARACTERISTICS

All characteristics are per diode at $T_i = 25$ °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{F}	Forward voltage	$I_F = 10 \text{ A}; \underline{T}_i = 125^{\circ}\text{C}$	-	0.61	0.7	V
		$I_F = 20 \text{ A}, T_1 = 125 ^{\circ}\text{C}$	-	0.74	0.85	V
		$I_{\rm F} = 20 \text{ A}$	-	0.88	0.95	V
I _R	Reverse current	$\dot{V}_{B} = V_{BWM}$	-	5	150	μĄ
		$V_{\rm B} = V_{\rm BWM}$; $T_{\rm j} = 125^{\circ}{\rm C}$	-	5	15	mΑ
C_{d}	Junction capacitance	$V_{\rm B} = 5 \text{ W}, \text{ f} = 1 \text{ MHz}, T_{\rm j} = 25 ^{\circ}\text{C} \text{ to } 125 ^{\circ}\text{C}$	-	420	-	рF

PBYR20100CT, PBYR20100CTB series

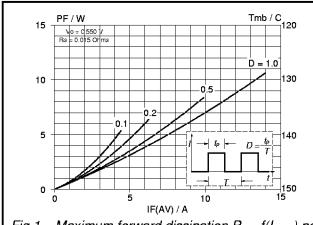


Fig.1. Maximum forward dissipation $P_F = f(I_{F(AV)})$ per diode; square current waveform where $I_{F(AV)} = I_{F(RMS)} \times \sqrt{D}$.

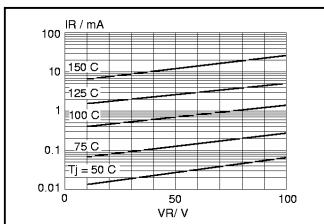


Fig.4. Typical reverse leakage current per diode; $I_R = f(V_R)$; parameter T_j

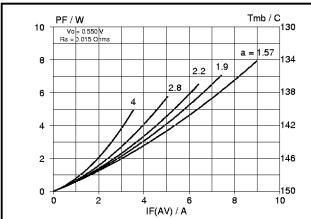


Fig.2. Maximum forward dissipation $P_F = f(I_{F(AV)})$ per diode; sinusoidal current waveform where a = f orm factor = $I_{F(BMS)} / I_{F(AV)}$.

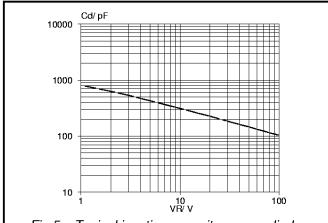


Fig.5. Typical junction capacitance per diode; $C_d = f(V_R)$; f = 1 MHz; $T_j = 25$ °C to 125°C.

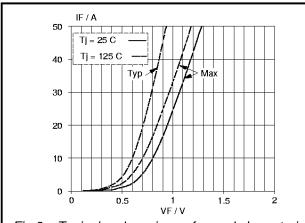


Fig.3. Typical and maximum forward characteristic $I_F = f(V_F)$; parameter T_i

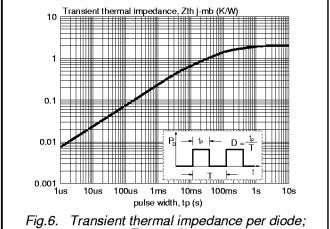
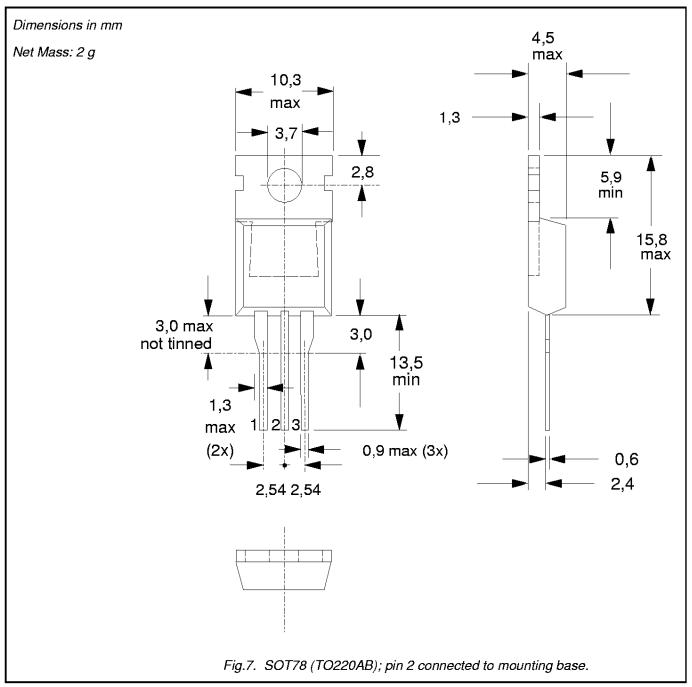


Fig.6. Transient thermal impedance per diode; $Z_{th j-mb} = f(t_p)$.

PBYR20100CT, PBYR20100CTB series

MECHANICAL DATA



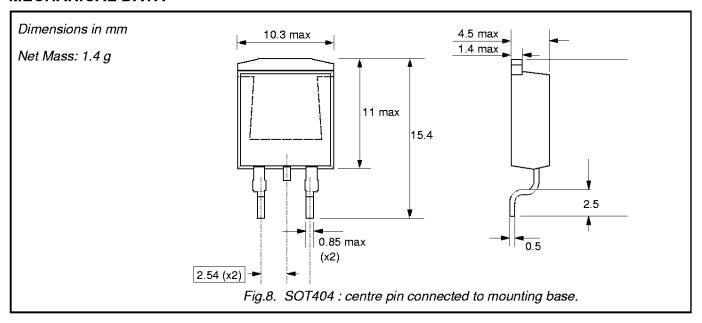
- Refer to mounting instructions for SOT78 (TO220) envelopes.
 Epoxy meets UL94 V0 at 1/8".

Philips Semiconductors Product specification

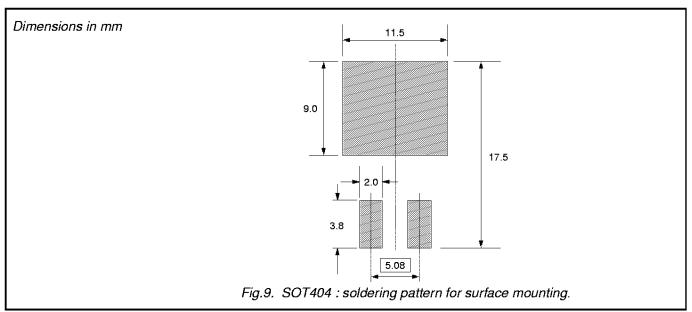
Rectifier diodes Schottky barrier

PBYR20100CT, PBYR20100CTB series

MECHANICAL DATA



MOUNTING INSTRUCTIONS



Notes

1. Epoxy meets UL94 V0 at 1/8".

Philips Semiconductors Product specification

Rectifier diodes Schottky barrier

PBYR20100CT, PBYR20100CTB series

DEFINITIONS

Data sheet status					
Objective specification This data sheet contains target or goal specifications for product development.					
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.				
Product specification This data sheet contains final product specifications.					
Limiting values					

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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